

Quarterly Reliability Monitoring Results

Quarters: 04/2018 to 03/2019

Based on structural similarity

Supplier Nexperia B.V.		User Part Number PBSS4612PA					
Nexperia DHAM Small Signal Bipolar Transistor							
MCD package							
Test		Test Conditions	Duration	# Lots	# Quantity	# Rejects	
	TEST Pre- and Post-Stress						
# 1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below	
# 2	PC Preconditioning	JESD22-A113 Bake Tamb = 125 °C Soak Tamb = 85 °C, RH = 85% Reflow soldering	24 hours 168 hours 3 cycles	156	12480	0	
# 5	HTRB High Temperature Reverse Bias	MIL-STD-750-1 M1038 Method A Tj = Tjmax, Vr = 100% of max. datasheet reverse voltage	1000 hours	154	12320	0	
# 7	TC Temperature Cycling	JESD22-A104 -55 °C to Tjmax, not to exceed 150°C	1000 cycles	39	3120	0	
# 8	AC Autoclave	JESD22-A102 Tamb = 121 °C, RH = 100 % Pressure = 205 kPa (29.7 psia)	96 hours	39	3120	0	
# 9	H3TRB High Humidity High Temperature Reverse Bias	JESD22-A101 Tamb = 85 °C, RH = 85%, VR > 80 % of rated reverse voltage	1000 hours	39	3120	0	
# 10	IOL Intermittent Operating Life	MIL-STD-750 Method 1037 ton = toff, devices powered to insure ΔTj =	1000 hours	39	3120	0	
# 20	RSH Resistance to Solder Heat	JESD22-A111 260 °C ± 5 °C	10 s	n.a.	n.a.	n.a.	
# 21	SD Solderability	J-STD-002 Test method B and D		117	1170	0	

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test # 5) Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	12320	0	0,34	2.90E+09

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